



30V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
	19mΩ @ V _{GS} = 4.5V	15A
001/	25mΩ @ V _{GS} = 2.5V	14A
30V	40mΩ @ V _{GS} = 1.8V	10A
	120mΩ @ V _{GS} = 1.5V	6A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Management Application
- Power Management Functions
- DC-DC Converters

Features

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- · Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

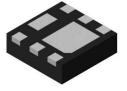
Mechanical Data

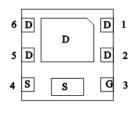
- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 4
- Weight: 0.007 Grams (Approximate)

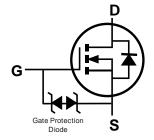
U-DFN2020-6 (Type F)











Top View

Bottom View

Pin Out Bottom View

Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3020UFDF-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel
DMN3020UFDF-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

Site 1



2F = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2015	 2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	С	 Η		J	K	L	М	Ν	0	Р	R

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Site 2



2F = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Year	2015	 2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	5	 0	1	2	3	4	5	6	7	8	9

Week	1-26	27-52	53
Code	A-Z	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Υ	Z



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	30	V		
Gate-Source Voltage	V _{GSS}	±12	V		
Continuous Dusin Courset (Nata CVV)	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +70^{\circ}C$	l _D	15 13	А
Continuous Drain Current (Note 6) V _{GS} = 4.5V	t<5s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	10.4 8.3	А
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%	6)		I _{DM}	40	Α
Continuous Source-Drain Diode Current (Note 6)	I _S	2.2	А		
Avalanche Current (Note 7) L = 0.1mH	I _{AS}	17	Α		
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	15	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	Pn	0.73	- W	
Total Power Dissipation (Note 5)	$T_A = +70$ °C	PD	0.47		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	171	°C/W	
Thermal Resistance, Junction to Ambient (Note 3)	t<5s	Көја	112		
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	D-	2.03	W	
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	P_D	1.30		
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	63	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<5s	$R_{\theta JA}$	40		
Thermal Resistance, Junction to Case	Steady State	$R_{ heta JC}$	18		
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 8)								
Drain-Source Breakdown Voltage	BV _{DSS}	30	1	_	V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	1	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$		
Gate-Source Leakage	I _{GSS}		1	±10	μΑ	$V_{GS} = \pm 10V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 8)								
Gate Threshold Voltage	V _{GS(TH)}	0.4	0.6	1.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$		
			16	19		$V_{GS} = 4.5V, I_D = 4.5A$		
Static Drain-Source On-Resistance	D		19	25	mΩ	$V_{GS} = 2.5V, I_D = 3.5A$		
Static Drain-Source On-Nesistance	R _{DS(ON)}		26	40	11122	$V_{GS} = 1.8V, I_D = 2.0A$		
			32	120		$V_{GS} = 1.5V, I_D = 1.0A$		
Diode Forward Voltage	V_{SD}	_	0.6	1.2	V	$V_{GS} = 0V, I_{S} = 1.0A$		
DYNAMIC CHARACTERISTICS (Note 9)								
Input Capacitance	C _{iss}	-	1304	-		V 45V V 0V		
Output Capacitance	C _{oss}	I	87	l	pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz		
Reverse Transfer Capacitance	C _{rss}	-	80	_		1 = 1.000112		
Gate Resistance	R_{g}	_	1.3	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$		
Total Gate Charge (V _{GS} = 4.5V)	Q_g	-	15	_				
Total Gate Charge (V _{GS} = 8V)	Q_g	_	27		nC	V _{DS} = 15V. I _D = 4.5A		
Gate-Source Charge	Q _{gs}	_	2.0	_	nc nc	$V_{DS} = 15V, I_D = 4.5A$		
Gate-Drain Charge	Q_{gd}	_	2.1	_				
Turn-On Delay Time	t _{D(ON)}	_	4.1	_				
Turn-On Rise Time	t _R	_	4.8	_	20	$V_{DS} = 15V, V_{GS} = 4.5V,$		
Turn-Off Delay Time	t _{D(OFF)}	_	20.5	_	ns	$R_G = 1\Omega$, $I_D = 4.5A$		
Turn-Off Fall Time	t _F	_	3.2	_				
Reverse Recovery Time	t _{RR}	_	7.1	_	ns	1 4 0 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4		
Reverse Recovery Charge	Q_{RR}	_	1.7	_	nC	$I_F = 1.0A$, di/dt = 100A/ μ s		

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

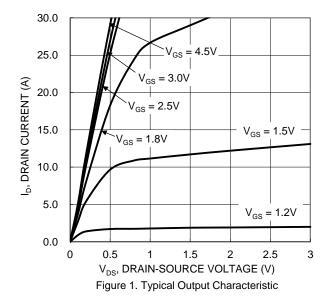
^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

^{7.} IAS and EAS ratings are based on low frequency and duty cycles to keep $T_J = +25$ °C.

^{8.} Short duration pulse test used to minimize self-heating effect.

^{9.} Guaranteed by design. Not subject to product testing.





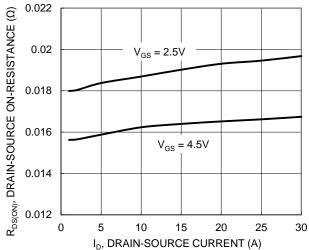


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

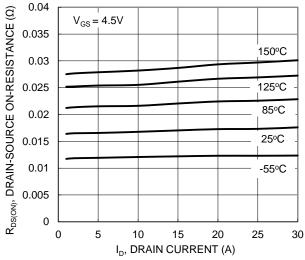
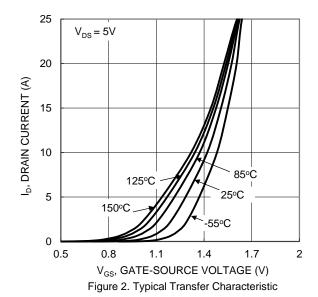


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



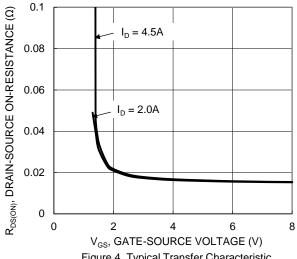


Figure 4. Typical Transfer Characteristic

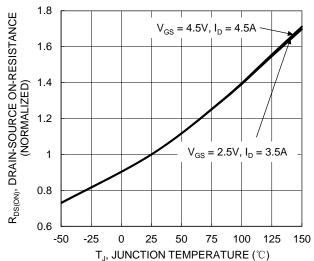
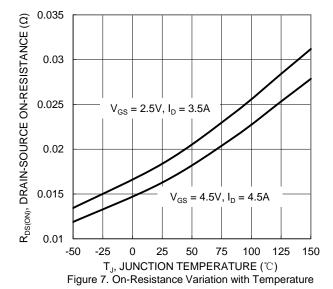
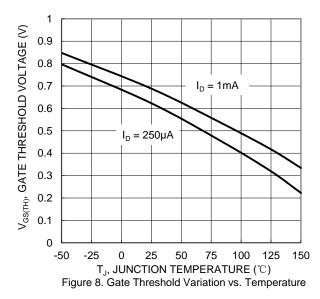
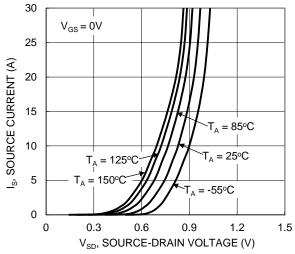


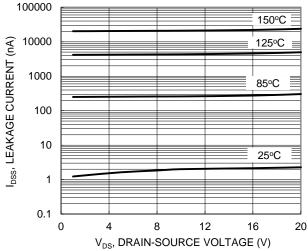
Figure 6. On-Resistance Variation with Temperature











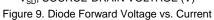
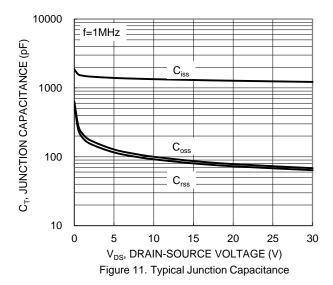
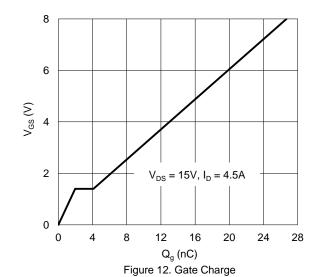
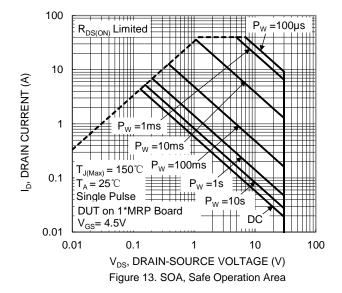


Figure 10. Typical Drain-Source Leakage Current vs. Voltage









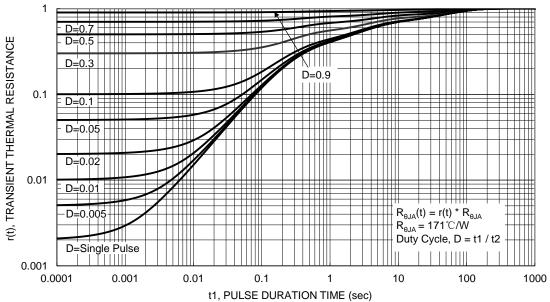


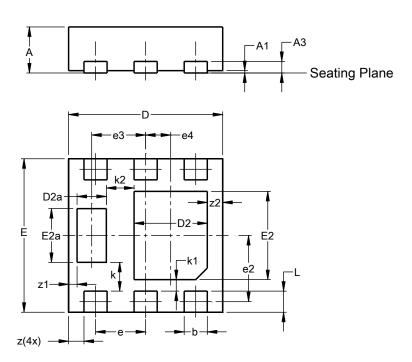
Figure 14. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

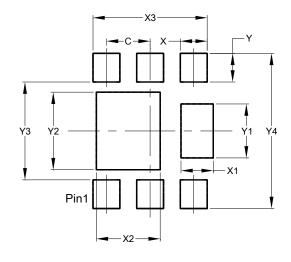


	U-DFN2020-6							
		oe F)						
Dim	Min	Max	Тур					
Α	0.57	0.63	0.60					
A1	0.00	0.05	0.03					
A3	1	-	0.15					
b	0.25	0.35	0.30					
D	1.95	2.05	2.00					
D2	0.85	1.05	0.95					
D2a	0.33	0.43	0.38					
Е	1.95	2.05	2.00					
E2	1.05	1.25	1.15					
E2a	0.65	0.75	0.70					
е		0.65 BS	С					
e2).863 BS	SC					
е3		0.70 BS	С					
e4	().325 BS	SC					
k		0.37 BS						
k1		0.15 BS						
k2		0.36 BS	-					
L	0.225	0.325	0.275					
Z		0.20 BS						
z 1	0.110 BSC							
z2		0.20 BS	С					
All C	imens	ions in	mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
С	0.650
Х	0.400
X1	0.480
X2	0.950
Х3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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